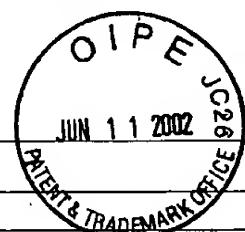


Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)



Sheet 1 of 2

Complete if Known

Application Number	09/945507
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Unknown

Attorney Docket No: 01303.014US1

US PATENT DOCUMENTS

Examiner Initials *	Cite No ¹	USP Document No	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures appear
		US-4412902	11/01/1983	Michikami, Osamu, et al	
SL		US-4780424	10/25/1988	Holler, Mark A	
		US-5350738	09/27/1994	Hase, Takashi, et al	
		US-5691230	11/25/1997	Forbes, L.	
		US-5801401	09/01/1998	Forbes, L.	
		US-5852306	12/22/1998	Forbes, Leonard	
GP		US-5936274	08/10/1999	Forbes, L., et al	
		US-5981350	11/09/1999	Geusic, J. E., et al	
		US-6025627	02/15/2000	Forbes, L., et al	
		US-6031263	02/29/2000	Forbes, L., et al	
		US-6134175	10/17/2000	Forbes, L., et al	
		US-6143636	11/07/2000	Forbes, L., et al	
GD		US-6208164	03/27/2001	Noble, W. P., et al	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No ¹	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures appear	T ²

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item(book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SL		ARYA, S., "Conduction Properties of Thin Al ₂ O ₃ Films", <u>Thin Solid Films</u> , 91, (1982), pp. 363-374	
SL		DIPERT, BRIAN., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, (October 1993), 48-52	
SL		ELDRIDGE, J.M., "Growth of Thin PbO Layers on Lead Films", <u>Surface Science</u> , Vol. 40, (1973), 512-530	
SL		ELDRIDGE, J., "Measurement of Tunnel Current Density in a Metal-Oxide-Metal System as a Function of Oxide Thickness", <u>Proc. 12th Intern. Conf. on Low Temperature Physics</u> , (1971), pp. 427-428	
SL		GREINER, J.G., "Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma", <u>Journal of Applied Physics</u> , vol. 42, no. 12, (November 1971), 5151-5155	
SL		GREINER, J., "Oxidation of lead films by rf sputter etching in an oxygen plasma", <u>Journal of Applied Physics</u> , 45(1), (1974), pp. 32-37	
SL		GUNDLACH, K., "Logarithmic Conductivity of Al-Al ₂ O ₃ -Al Tunneling Junctions Produced by Plasma and by Thermal Oxidation", <u>Surface Science</u> , 27, (1971),	

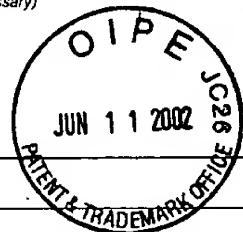
EXAMINER

SON DINH

DATE CONSIDERED

6/11/03

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(Use as many sheets as necessary)

Complete if Known

Application Number	09/945507
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Unknown

Sheet 2 of 2

Attorney Docket No: 01303.014US1

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the item(book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CA		pp. 125-141	
CA		HURYCH, Z. "Influence of Non-Uniform Thickness of Dielectric Layers on Capacitance and Tunnel Currents", <u>Solid-State Electronics</u> , vol. 9, (1966),967-979	
		KUBASCHEWSKI, O. "Oxidation of Metals and Alloys", <u>Butterworths</u> , London, (1962),53-63	
		LUAN, H.F., "High Quality Ta ₂ O ₅ Gate Dielectrics with T _{ox,eq} <10Å", <u>IEDM Technical Digest</u> , (1999),141-143	
		MASUOKA, FUJIO., "A 256K flash EEPROM using Triple Polysilicon Technology", <u>1985 IEEE International Solid-State Circuits Conference. Digest of Technical Papers</u> , (02/1985),168-169	
		MASUOKA, FUJIO., "A new Flash E ² PROM Cell using Triple Polysilicon Technology", <u>International Electron Devices Meeting. Technical Digest</u> , (12/1984),464-467	
		MORI, S., "Reliable CVD Inter-Poly Dielectrics for Advanced E&EEPROM", <u>1985 Symposium on VSLI Technology. Digest of Technical Papers</u> , (1985),16-17	
		PASHLEY, RICHARD D., "Flash Memories: the best of two worlds", <u>IEEE Spectrum</u> , (December/1989),30-33	
		POLLACK, S., "Tunneling Through Gaseous Oxidized Films of Al ₂ O ₃ ", <u>Transactions of the Metallurgical Society of AIME</u> , 233, (1965),pp. 497-501	
		ROBERTSON, J., "Schottky Barrier height of Tantalum oxide, barium strontium titanate, lead titanate, and strontium bismuth tantalate", <u>Applied Physics Letters</u> , vol. 74, no. 8, (02/22/1999),1168-1170	
		SHI, Y., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters</u> , 19(10), (October 1998),pp. 388-390	
CA		SIMMONS, J., "Generalized Formula for the Electric Tunnel Effect between Similar Electrodes Separated by a Thin Insulating Film", <u>Journal of Applied Physics</u> , 34(6), (1963),pp. 1793-1803	
SD		SZE, S., <u>Physics of Semiconductor Devices</u> , Second Edition, (1981),pp. 553-556	

EXAMINER

SON DINH

DATE CONSIDERED

6/11/03